

Ordering number : ENA1358



SANYO Semiconductors

DATA SHEET

N-Channel and P-Channel Silicon MOSFETs
ECH8660 — General-Purpose Switching Device Applications

Features

- The ECH8660 incorporates an N-channel MOSFET and a P-channel MOSFET that feature low ON-resistance and high-speed switching , thereby enabling high-density mounting.
- 4V drive.
- Halogen free compliance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		30	-30	V
Gate-to-Source Voltage	V _{GSS}		±20	±20	V
Drain Current (DC)	I _D		4.5	-4.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	30	-30	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (1200mm ² ×0.8mm) 1unit	1.3		W
Total Dissipation	P _T	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D =30V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V

Marking : TF

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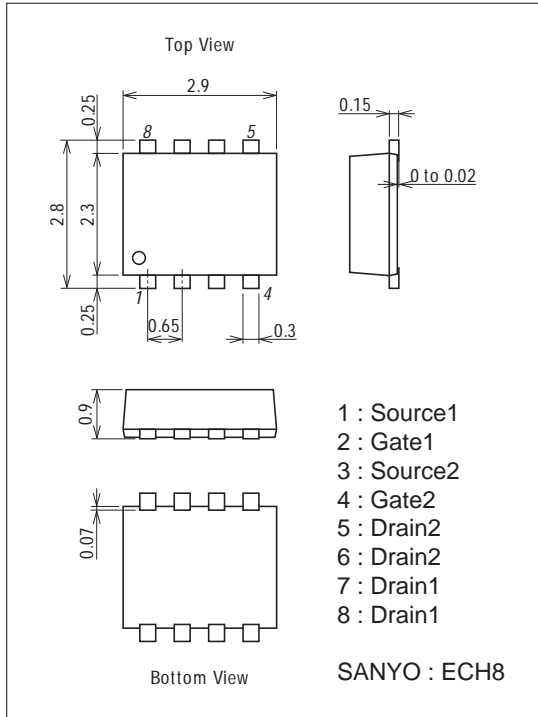
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=2A$	1	1.66		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=2A, V_{GS}=10V$		45	59	$m\Omega$
	$R_{DS(on)2}$	$I_D=1A, V_{GS}=4.5V$		85	119	$m\Omega$
	$R_{DS(on)3}$	$I_D=1A, V_{GS}=4V$		110	155	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		240		μF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		45		μF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		30		μF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		6.2		ns
Rise Time	t_r	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		17		ns
Fall Time	t_f	See specified Test Circuit.		7.5		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=4.5A$		4.4		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=4.5A$		1.1		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=4.5A$		0.64		nC
Diode Forward Voltage	V_{SD}	$I_S=4.5A, V_{GS}=0V$		0.84	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0V$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.2		-2.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-2A$	2.5	4.2		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-2A, V_{GS}=-10V$		45	59	$m\Omega$
	$R_{DS(on)2}$	$I_D=-1A, V_{GS}=-4.5V$		71	100	$m\Omega$
	$R_{DS(on)3}$	$I_D=-1A, V_{GS}=-4V$		82	115	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		430		μF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		105		μF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		75		μF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7.5		ns
Rise Time	t_r	See specified Test Circuit.		26		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		45		ns
Fall Time	t_f	See specified Test Circuit.		35		ns
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4.5A$		10		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4.5A$		2.0		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-4.5A$		2.5		nC
Diode Forward Voltage	V_{SD}	$I_S=-4.5A, V_{GS}=0V$		-0.85	-1.2	V

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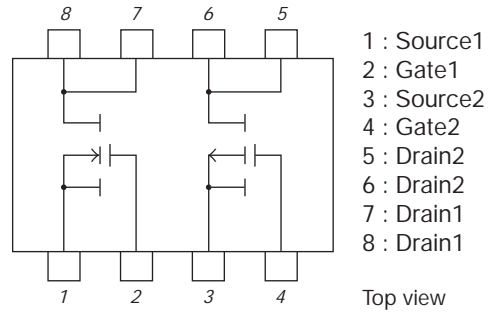
Package Dimensions

unit : mm (typ)

7011A-001

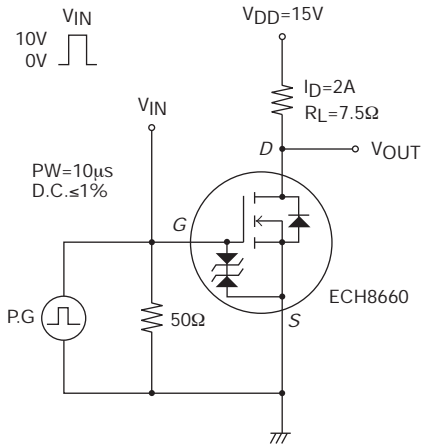


Electrical Connection

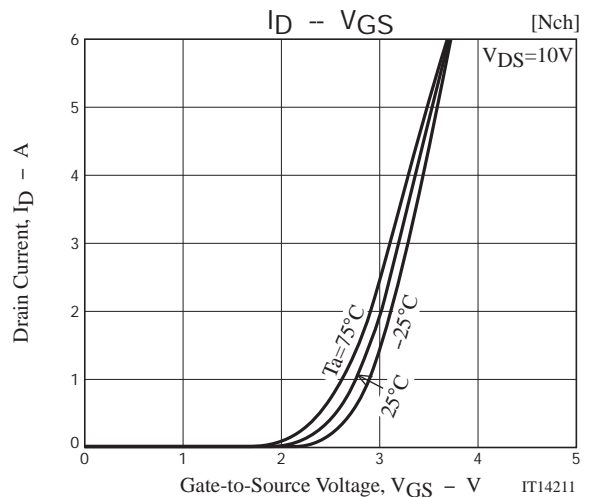
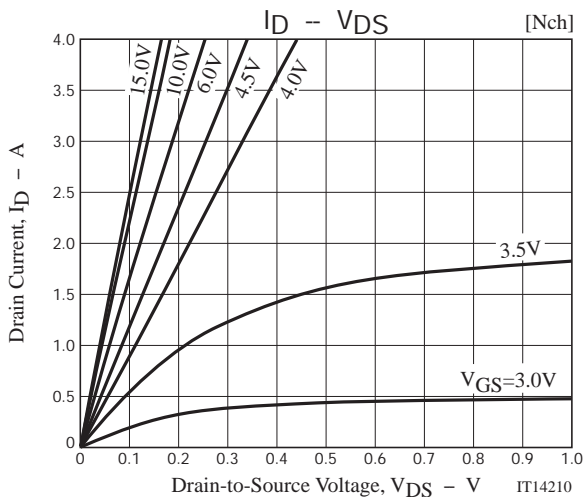
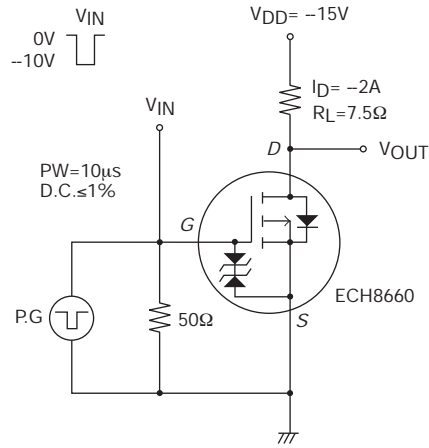


Switching Time Test Circuit

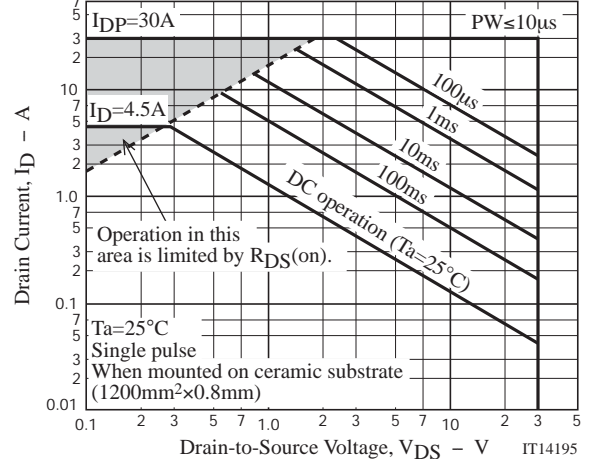
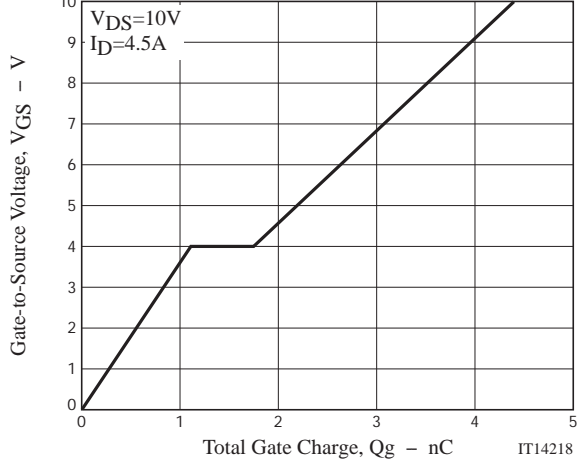
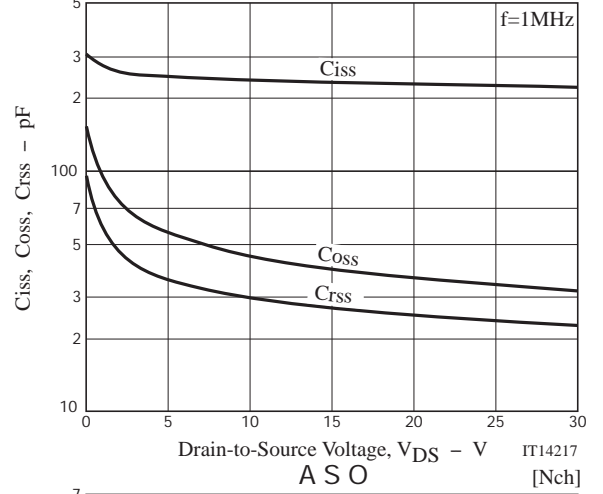
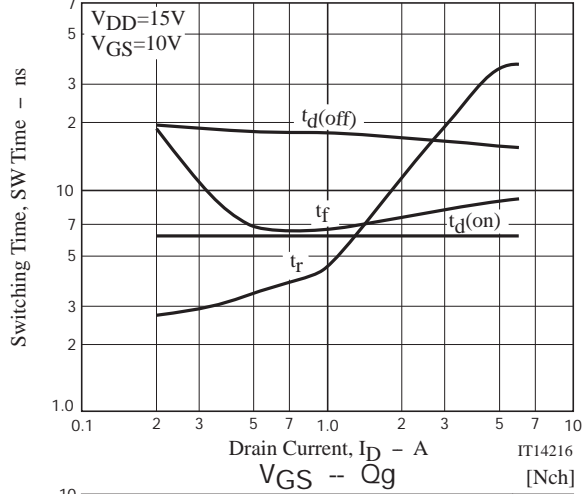
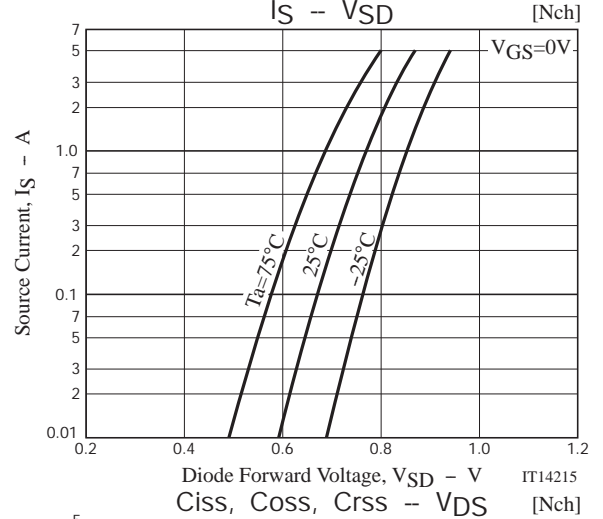
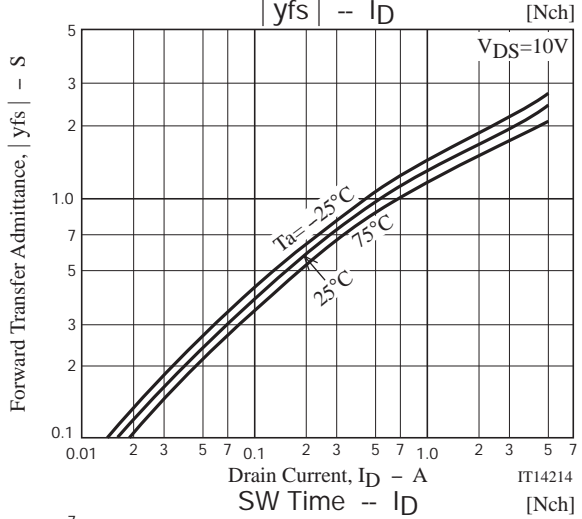
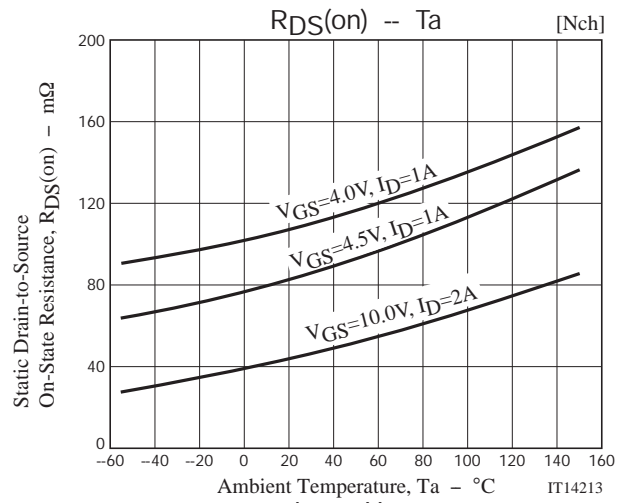
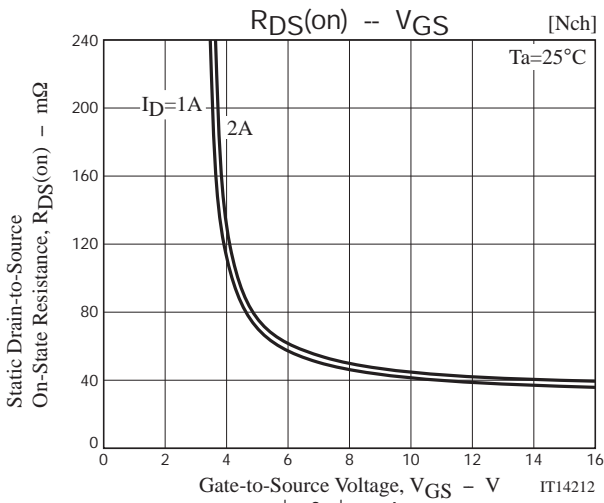
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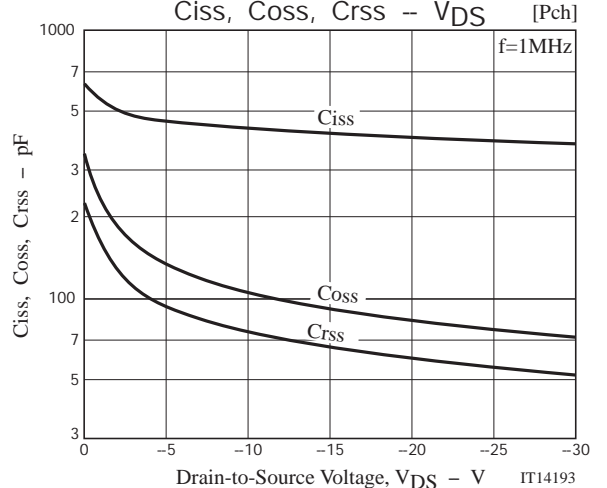
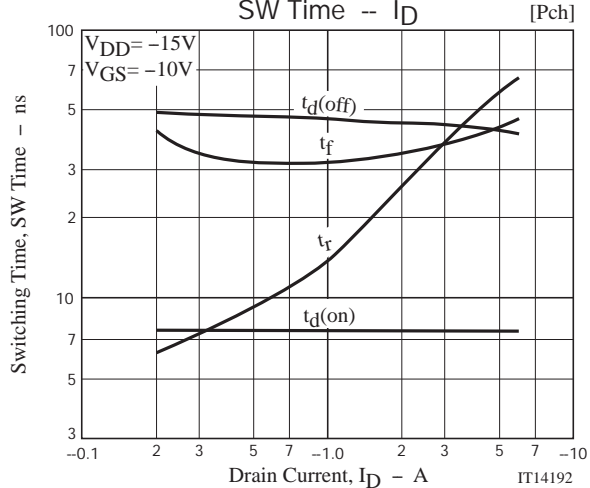
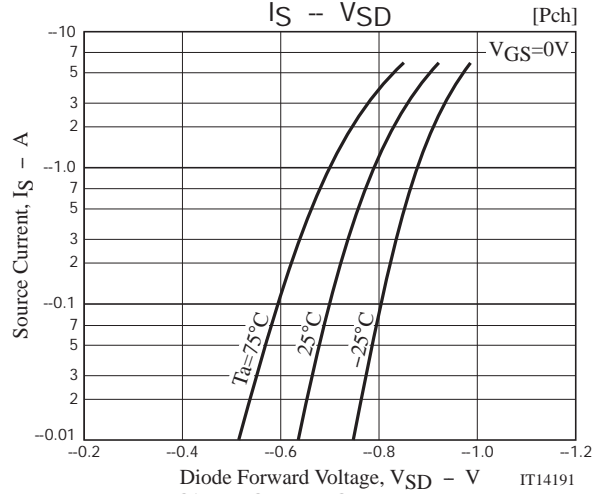
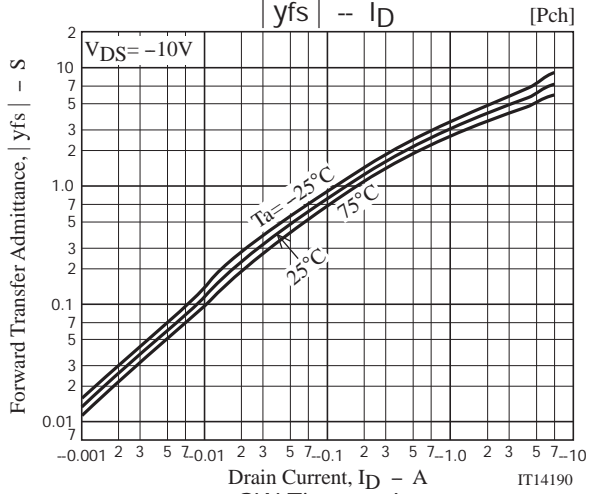
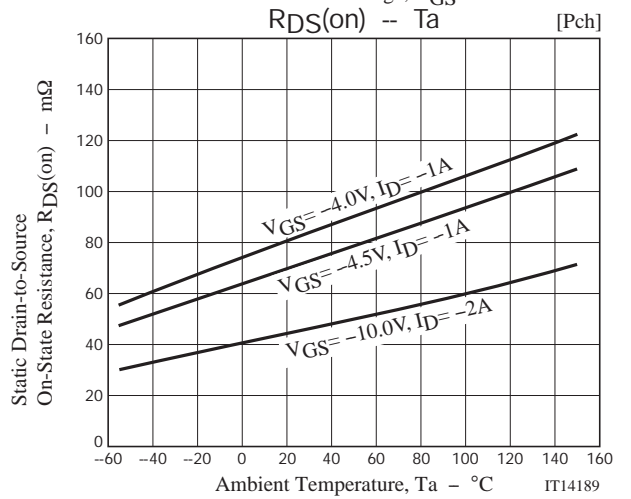
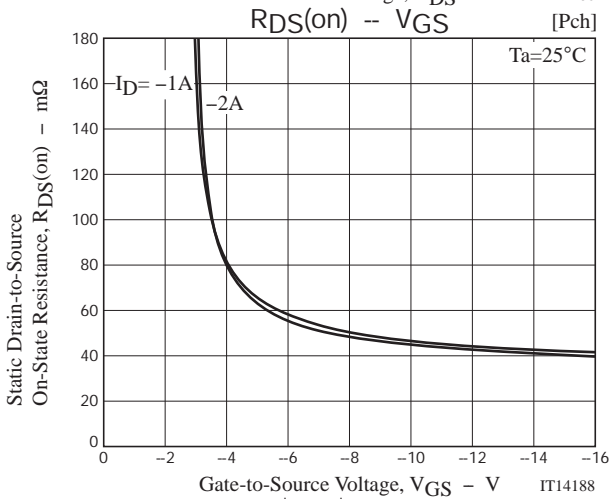
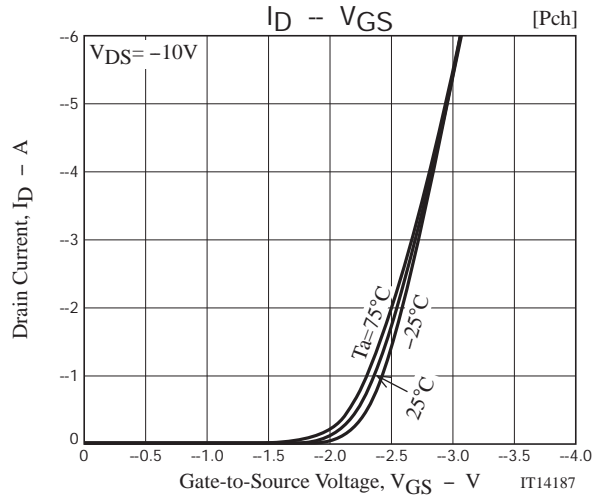
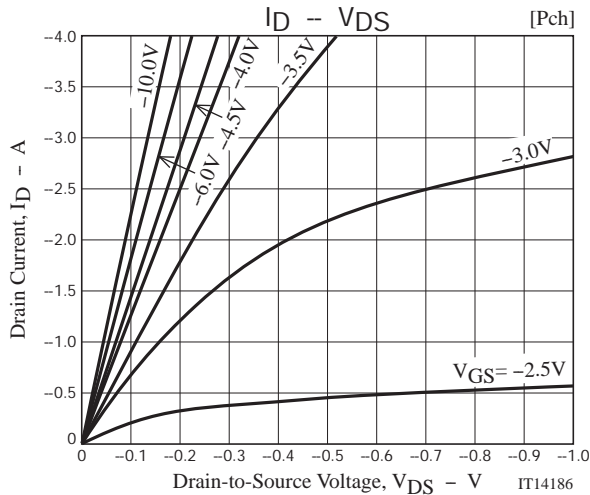
[P-channel]



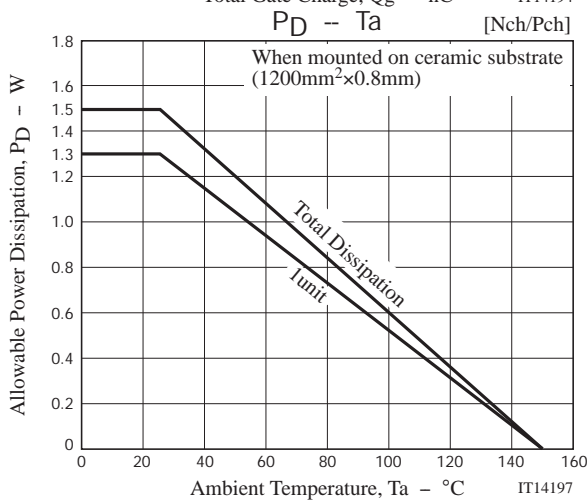
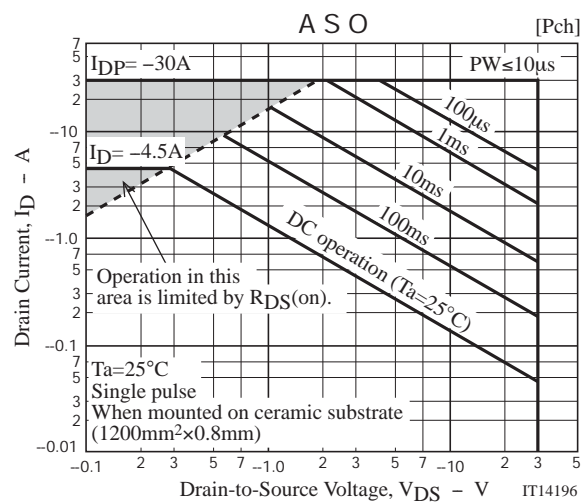
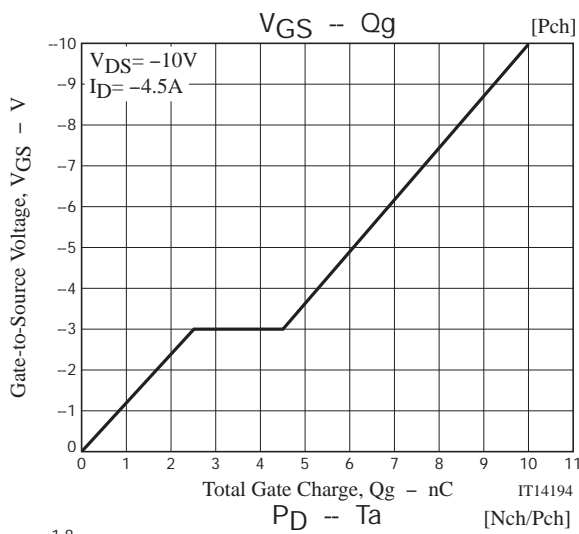
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Note on usage : Since the ECH8660 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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